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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>		Application Number	Filed Herewith 10/676,695
		Filing Date	9/30/2003
		First Named Inventor:	Fu-Chieh Hsu
		Examiner name: A. Wilson (Parent case)	GROUP: 2815 (Parent case)
Sheet 1 of 1	Attorney Docket Number		MST-013-1D

U.S. PATENT DOCUMENTS

Examiner Initials*	Cited No. ¹	U.S. Patent Document Number	Kind Code ² (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines Where Relevant Info. Appear
<i>ae</i>	A1	5937296		Arnold	08-10-1999	<i>✓</i>
<i>f</i>	A2	6281557	B1	Trueby et al.	08-28-2001	
	A3	5739567		Wong	04-14-1998	
	A4	5216269		Middelhoek et al.	06-01-1993	
	A5	5264716		Kenney	11-23-1993	
	A6	5672536		Wu et al.	09-30-1997	
	A7	5708290		Cacciola et al.	01-13-1998	
<i>ae</i>	A8	5789286		Subbanna	08-04-1998	<i>✓</i>

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cited No. ¹	Foreign Patent Document Office ³ Number ⁴	Kind Code ⁵ (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines Where Relevant Info. Appear	T ⁶

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>ae</i>	Article entitled "A Capacitor-Less 1T-DRAM Cell", IEEE Electron Device Letters, Vol. 23, No. 2, Feb. 2002, by S. Okhonin et al., pages 85-87
<i>ae</i>	Article entitled "Memory Design Using One-Transistor Gain Cell on SOI" ISSCC 2002/Session 9/DRAM And Ferroelectric Memories/9.1; by Takashi Ohsawa et al.; pages 452-454. <i>NO MONTH GIVEN</i>
EXAMINER <i>A. Wilson</i>	DATE CONSIDERED <i>10/21/04</i>

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.